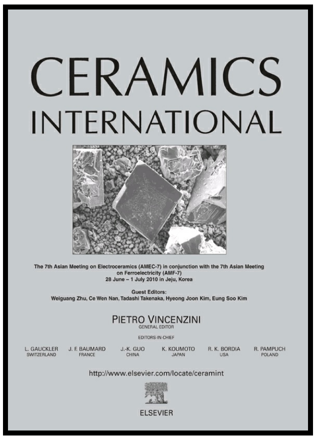
Surface morphology evolution and optoelectronic properties of heteroepitaxial Si-doped β-Ga_2O_3 thin films grown by metal-organic chemical vapor deposition

Daqiang Hu, Ying Wang, Shiwei Zhuang, Xin Dong, Yuantao Zhang, Jingzhi Yin, Baolin Zhang, Yuanjie Lv, Zhihong Feng, Guotong Du



www.elsevier.com/locate/ceri

PII: S0272-8842(17)32534-8
DOI: https://doi.org/10.1016/j.ceramint.2017.11.079
Reference: CERI16734

To appear in: *Ceramics International*

Received date: 20 October 2017
Revised date: 9 November 2017
Accepted date: 11 November 2017

Cite this article as: Daqiang Hu, Ying Wang, Shiwei Zhuang, Xin Dong, Yuantao Zhang, Jingzhi Yin, Baolin Zhang, Yuanjie Lv, Zhihong Feng and Guotong Du, Surface morphology evolution and optoelectronic properties of heteroepitaxial Si-doped β-Ga_2O_3 thin films grown by metal-organic chemical vapor deposition, *Ceramics International,* https://doi.org/10.1016/j.ceramint.2017.11.079

Surface morphology evolution and optoelectronic properties of heteroepitaxial Si-doped β-Ga_2O_3 thin films grown by metal-organic chemical vapor deposition

Daqiang Hu [a], Ying Wang [b], Shiwei Zhuang [a], Xin Dong* [a], Yuantao Zhang [a], Jingzhi Yin* [a], Baolin Zhang [a], Yuanjie Lv [c], Zhihong Feng [c], Guotong Du [a]

[a] State Key Laboratory on Integrated Optoelectronics, College of Electronic Science and Engineering, Jilin University, Qianjin Street 2699, Changchun 130012, China

[b] School of Science, University of Science and Technology Liaoning, Anshan 114051, China

[c] National Key Laboratory of Application Specific Integrated Circuit (ASIC), Hebei Semiconductor Research Institute, Shijiazhuang, 050051, China

E-mail address: dongx@jlu.edu.cn (Xin Dong)

E-mail address: yjz886666@163.com (Jingzhi Yin)

*Corresponding author: